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HOPPING CONDUCTIVITY IN THE PEIERLS GAP IN HYDRAZINE INTERCALATED TaS₂

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Abstract The hydrazine intercalation complexes formed with the layered compound 1T-TaS₂ exhibit very strong Fermi surface driven structural distortions. They are non-metallic below room temperature due to Anderson localization of states near the Fermi level which lies in the Peierls pseudo-gap. Resistivity, ρ , and thermopower, S , measurements indicate that transport is by variable range hopping, and a proportionality is demonstrated between $\ln \rho$ and $\sqrt{S/T}$ over a wide temperature range. The conduction mechanism in this intercalation complex may be compared with that in lightly-doped polyacetylene, in which the Fermi level also falls in the Peierls gap.

1T-TaS₂ belongs to a class of "two-dimensional" metals which have a layered structure and exhibit Fermi surface related structural phase transitions^{1,2}. Hydrazine may be intercalated reversibly between the layers^{3,4} and two complexes are produced, 3R_I with $0 < x < 2/3$ and 3R_{I,I} with $2/3 < x < 4/3$. Each shows a well-defined layer separation indicating one and two layers of hydrazine respectively between adjacent layers of the host material⁵.

The intercalated materials are non-metallic as shown in figure 1 where the resistivities of the $x = 2/3$ and $x = 4/3$ complexes are compared with that of the pure material which has an incommensurate to commensurate Peierls transition at $\sim 200\text{K}$ and shows weakly non-metallic behaviour below 50K. In a previous paper⁴ we present evidence for an intercalate induced enhancement of the Peierls pseudo-gap to $\sim 1\text{eV}$ in the 3R_{I,I} complex and for Anderson

localization of the electronic states near the Fermi level, E_F , which lies in this gap. We discuss here the mechanism of conduction in the light of recent transport measurements.

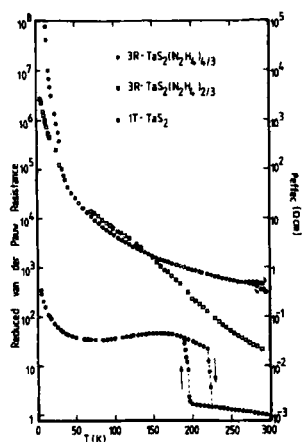


FIGURE 1 Resistivity of 1T-TaS₂ and the two hydrazine intercalation complexes

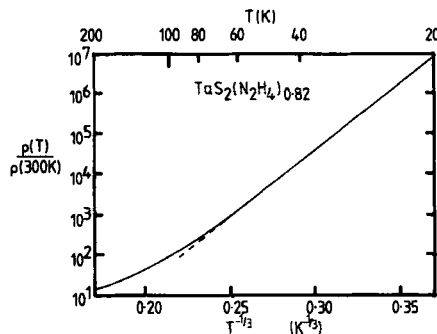


FIGURE 2 Logarithm of resistivity of TaS₂(N₂H₄)_{0.82} plotted against $T^{-1/3}$

The temperature dependences of the resistivity for both complexes do not show simple activated behaviour but for the 3R_{L.I} material, the plot in figure 2 shows that the two dimensional variable range hopping (VRH) relation $\rho = \rho_0 \exp[T_0/T]^{1/3}$ is approximately obeyed with $T_0 = 4.6 \times 10^5 \text{ K}$ (fitting below 100K). If we assume a localization length, α^{-1} , of 10 \AA , this value of T_0 corresponds to a density of states, $N(E_F) \sim 1.3 \times 10^{20} \text{ eV}^{-1} \text{ cm}^{-3}$ 4,7. Such a value is a factor of 100 below the typical metallic value for a d-band and is an acceptable value for E_F located in the Peierls pseudo-gap.

The thermopower, S , for the $3R_{I.I}$ complex is plotted in figure 3 and has a large negative value which shows little variation with temperature. For activation to a mobility edge at E_C , $S \propto (E_C - E_F)/k_B T$ and a strong temperature dependence is expected⁷. On the other hand, for VRH, $S = A(k_B/e)^2 \cdot \gamma \cdot (W^2/k_B T)$ where W is the most probable hopping energy at a given temperature, $\gamma = (1/N)(dN/dE)|_{E_F}$ and A is a constant with a model dependent value^{7,8,9} between 0.5 and 0.05. For VRH in a constant density of states $W \propto T^{3/4}$ in 3D and $W \propto T^{2/3}$ in 2D. Clearly the density of states is not constant (otherwise $\gamma = 0$) but a similar type of relation between W and T is expected which would lead only to a weak dependence of S on T (S is constant if $W \propto T^{1/2}$). We conclude that conduction in the $3R_{I.I}$ material is by VRH and not by activation to a mobility edge.

It is interesting to note that the resistivity in the VRH regime may be expressed as $\rho = \rho_0 \exp[(1+m)W/k_B T]$ where m is related to the effective dimensionality for hopping by $W \propto R^{-m}$ and R is the most probable hopping range at a given temperature. We may relate this with the expression for thermopower discussed above to obtain the relation $\ln \rho = \ln \rho_0 + (1+m)B \sqrt{(S/\gamma T)}$. Thus, for γ constant, $\ln \rho \propto \sqrt{(S/T)}$ for any dimensionality. This is the behaviour observed in figure 4 over a much wider range of temperature than the range over which $\ln \rho$ is proportional to $T^{-1/3}$ in figure 2.

From this plot we estimate a value $4 < \gamma < 40 \text{ eV}^{-1}$ (the range reflects the different values calculated for A). For an incommensurate PLD we expect E_F to lie in the middle of the Peierls pseudo-gap and hence a small value for γ . However, if the PLD is commensurate E_F will be displaced from the centre of the Peierls gap and γ may be quite large. We consider the value estimated for γ to be acceptable in the present case where the PLD is commensurate⁶.

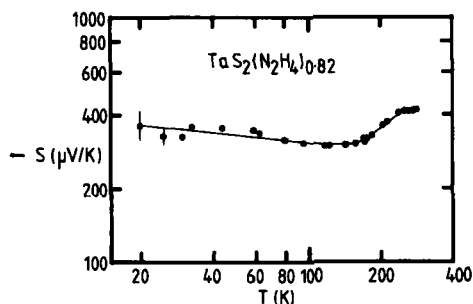


FIGURE 3 Thermopower vs. T in $\text{TaS}_2(\text{N}_2\text{H}_4)_{0.82}$

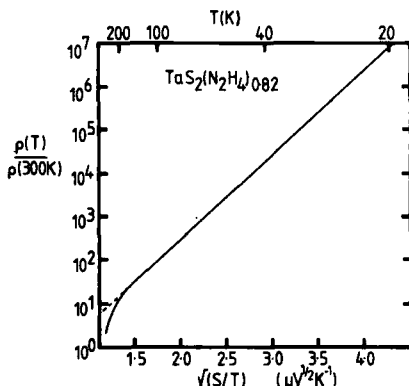


FIGURE 4 Logarithm of resistivity vs. square root of thermopower divided by temperature in $\text{TaS}_2(\text{N}_2\text{H}_4)_{0.82}$

Finally, we point out that a close relationship may exist between the conduction mechanism in the present intercalation complexes and that in lightly-doped samples of polyacetylene which exhibit non-metallic properties. In those samples the Fermi level should also lie in the Peierls gap, the gap between the soliton and conduction bands¹⁰.

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